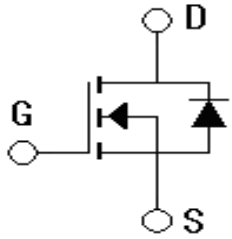
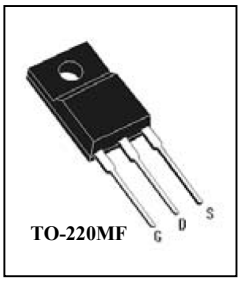
JCS20N65H

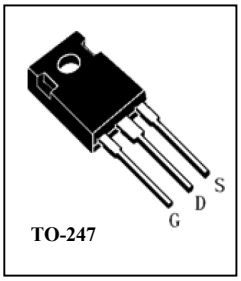
主要参数 MAIN CHARACTERISTICS

I_D	20A
V_{DSS}	650 V
Rdson-max (@Vgs=10V)	0.5Ω
Qg-typ	45nC

封装 Package







用途 APPLICATIONS

- 高频开关电源 High frequency switching mode power supply
- 电子镇流器 Electronic ballast
- LED 电源 LED power supply

产品特性 FEATURES

- 低栅极电荷 Low gate charge
- 低 C_{rss} (典型值 11pF) Low C_{rss} (typical 11pF)
- 开关速度快 Fast switching
- 产品全部经过雪崩测试 100% avalanche tested
- 高抗 dv/dt 能力 Improved dv/dt capability
- RoHS 产品 RoHS product

订货信息 ORDER MESSAGE

订 货 型 号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JCS20N65FH-F-B	JCS20N65FH-F-BR	N/A	N/A	JCS20N65FH	TO-220MF
JCS20N65WH-GE-B	JCS20N65WH-GE-BR	N/A	N/A	JCS20N65WH	TO-247

绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项 目 Parameter	符 号 Symbol	数 值 Value		单位 Unit
		JCS20N65WH	JCS20N65FH	
最高漏极－源极直流电压 Drain-Source Voltage	V_{DSS}	650		V
连续漏极电流 Drain Current -continuous	I_D T=25℃	20		A
	T=100℃	12.5		A
最大脉冲漏极电流（注 1） Drain Current – pulse（note 1）	I_{DM}	80		A
最高栅源电压 Gate-Source Voltage	V_{GSS}	±30		V
单脉冲雪崩能量（注 2） Single Pulsed Avalanche Energy（note 2）	E_{AS}	108		mJ
雪崩电流（注 1） Avalanche Current（note 1）	I_{AR}	20		A
重复雪崩能量（注 1） Repetitive Avalanche Energy （note 1）	E_{AR}	20.7		mJ
二极管反向恢复最大电压变化速率（注 3） Peak Diode Recovery dv/dt（note 3）	dv/dt	50		V/ns
耗散功率 Power Dissipation	P_D T_C=25℃	500	62.2	W
	-Derate above 25℃	4.0	0.5	W/℃
最高结温及存储温度 Operating and Storage Temperature Range	T_J，T_{STG}	-55～+150		℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300		℃

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

项　　目 Parameter	符　号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏－源击穿电压 Drain-Source Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V	650	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	I_D=250μA, referenced to 25℃	-	0.5	-	V/℃
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=650V,V_{GS}=0V, T_C=25℃	-	-	10	μA
		V_{DS}=520V, T_C=125℃	-	-	100	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	V_{DS}=0V, V_{GS} =30V	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	V_{DS}=0V, V_{GS} =-30V	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D=250μA	3.0	-	5.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS} =10V , I_D=10A	-	0.44	0.5	Ω
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{iss}	V_{DS}=25V, V_{GS} =0V, f=1.0MHz	-	2550	4000	pF
输出电容 Output capacitance	C_{oss}		-	250		pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	11		pF

电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_d(on)$	V_{DD}=300V,I_D=20A,R_G=25Ω （note 4，5）	-	56	128	ns
上升时间 Turn-On rise time	t_r		-	140	270	ns
延迟时间 Turn-Off delay time	$t_d(off)$		-	80	350	ns
下降时间 Turn-Off Fall time	t_f		-	50	120	ns
栅极电荷总量 Total Gate Charge	Q_g	V_{DS} =520V , I_D=20A V_{GS} =10V （note 4，5）	-	45	80	nC
栅一源电荷 Gate-Source charge	Q_{gs}		-	15.0	-	nC
栅一漏电荷 Gate-Drain charge	Q_{gd}		-	17	-	nC
漏一源二极管特性及最大额定值 **Drain-Source Diode Characteristics and Maximum Ratings**						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I_S		-	-	20	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	80	A
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=20A	-	-	1.45	V
反向恢复时间 Reverse recovery time	t_{rr}	V_{GS}=0V, I_S=20A dI_F/dt=100A/μs (note 4)	-	660	-	ns
反向恢复电荷 Reverse recovery charge	Q_{rr}		-	.9.3	-	μC

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max		单 位 Unit
		JCS20N65WH	JCS20N65FH	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.25	2.01	℃/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	29.8	39.7	℃/W

注释：

1：脉冲宽度由最高结温限制

2：L=0.5mH, I_{AS}=20A, V_{DD}=50V, R_G=25 Ω,起始结温 T_J=25℃

3：I_{SD} ≤9.5A,di/dt ≤300A/μs,VDD≤BV_{DSS},起始结温 T_J=25℃

4：脉冲测试：脉冲宽度≤300μs,占空比≤2%

5：基本与工作温度无关

Notes:

1：Pulse width limited by maximum junction temperature

2：L=0.5mH, I_{AS}=20A, V_{DD}=50V, R_G=25 Ω,Starting T_J=25℃

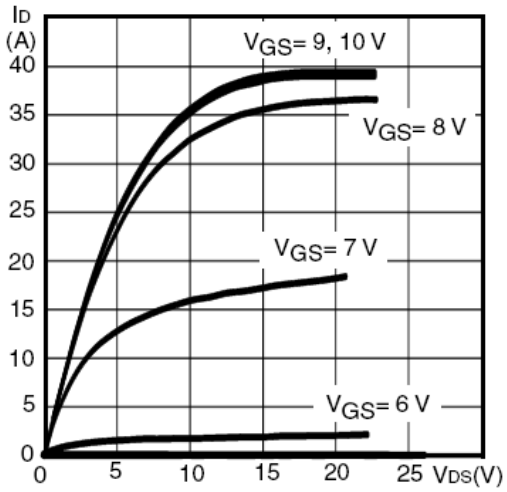
3：I_{SD} ≤9.5A,di/dt ≤300A/μs,VDD≤BV_{DSS}, Starting T_J=25℃

4：Pulse Test：Pulse Width ≤300μs,Duty Cycle≤2%

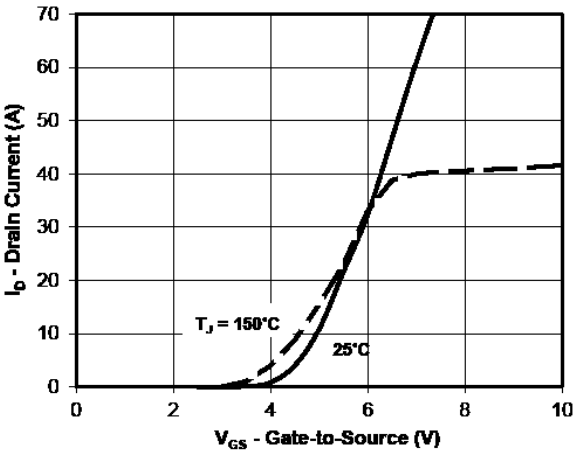
5：Essentially independent of operating temperature

特征曲线　ELECTRICAL CHARACTERISTICS (curves)

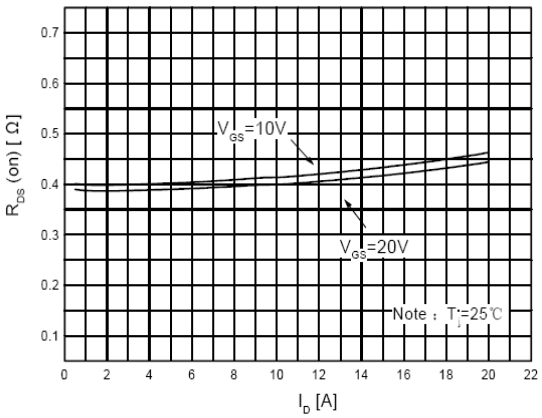
On-Region Characteristics



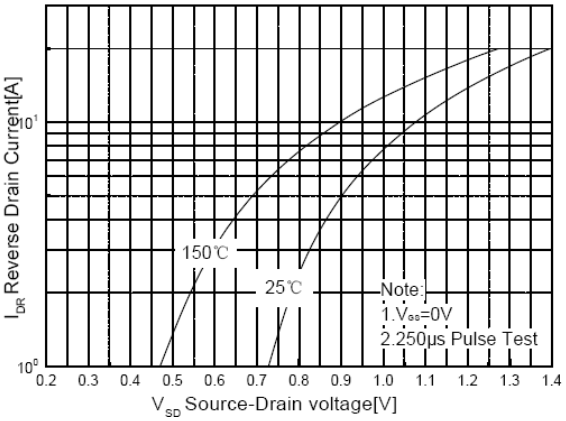
Transfer Characteristics



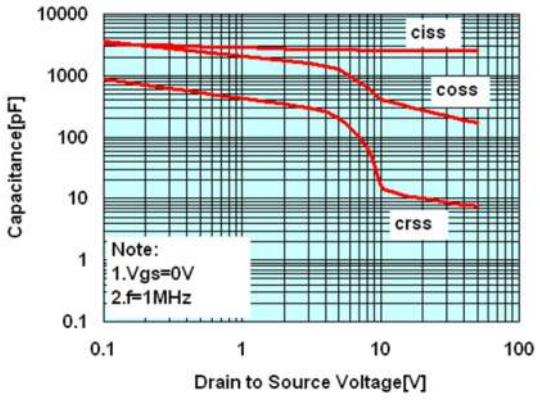
On-Resistance Variation vs. Drain Current and Gate Voltage



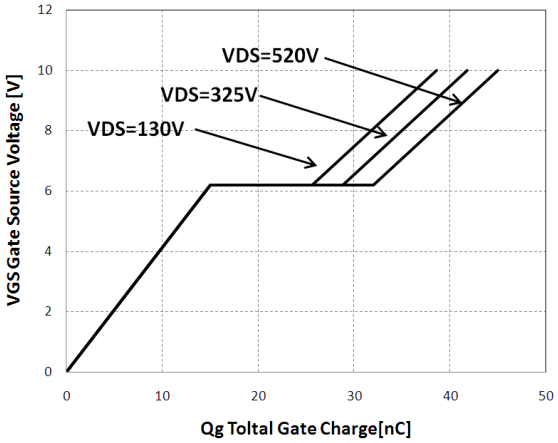
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics

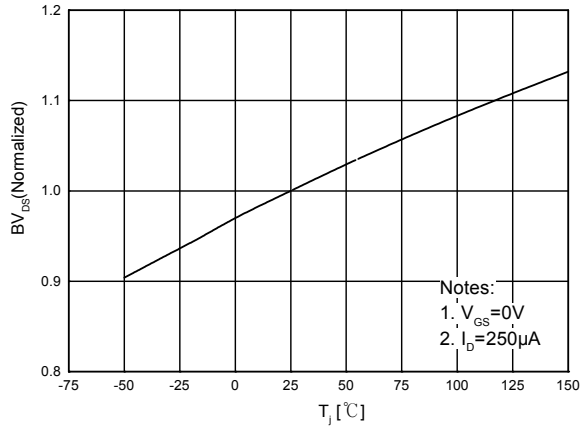


Gate Charge Characteristics

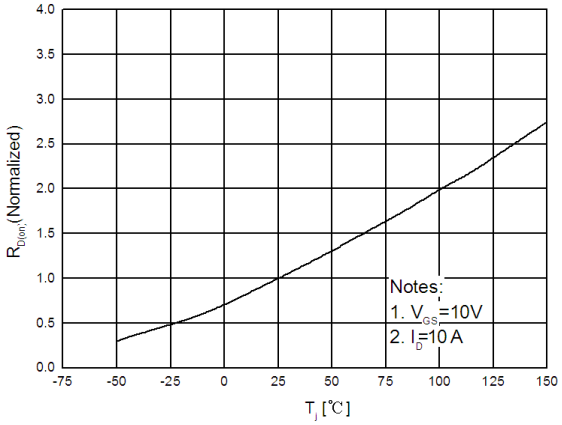


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Breakdown Voltage Variation vs. Temperature

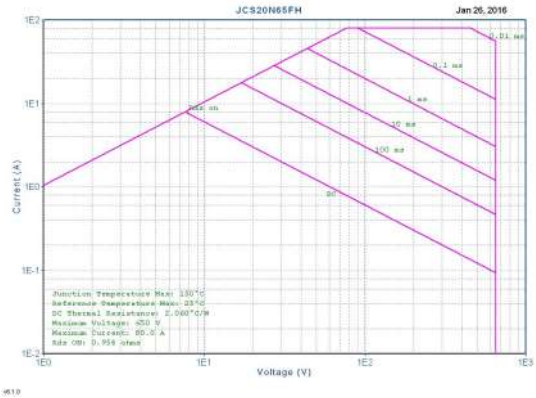


On-Resistance Variation vs. Temperature

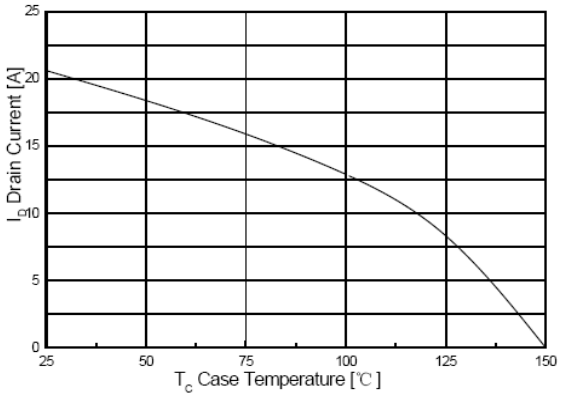


Maximum Safe Operating Area For JCS20N65WH

Maximum Safe Operating Area For JCS20N65FH

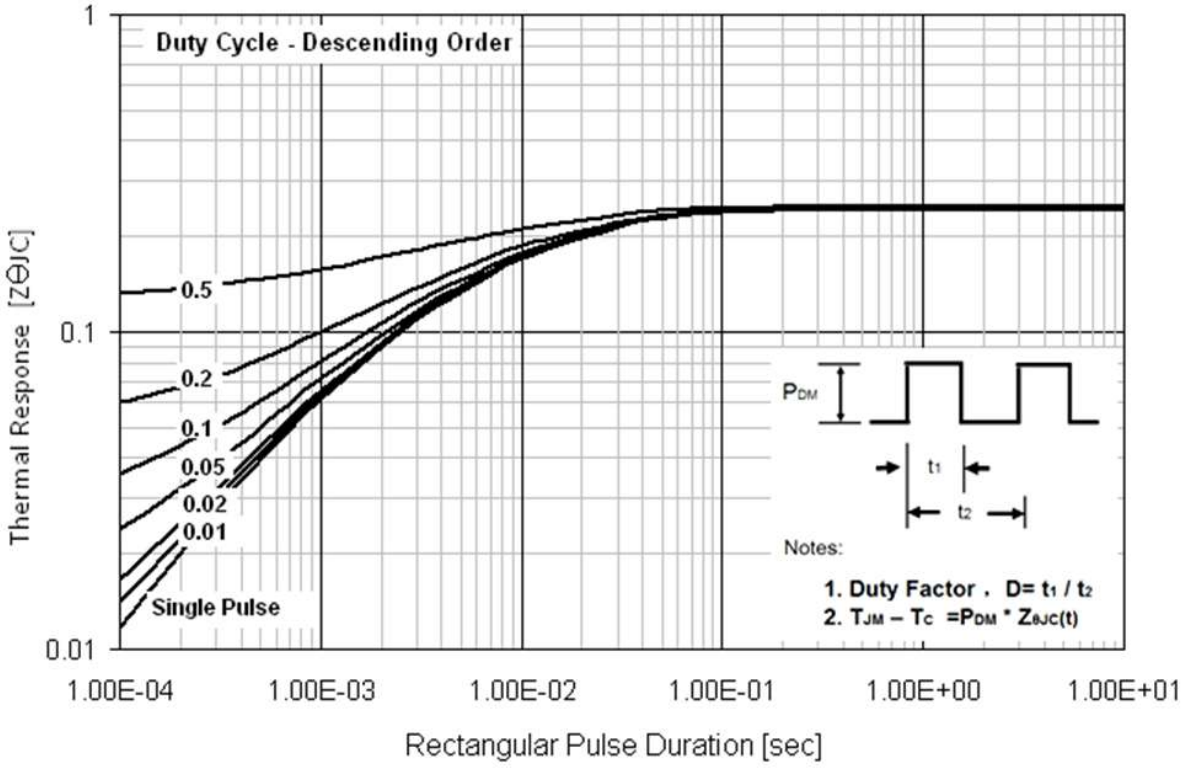


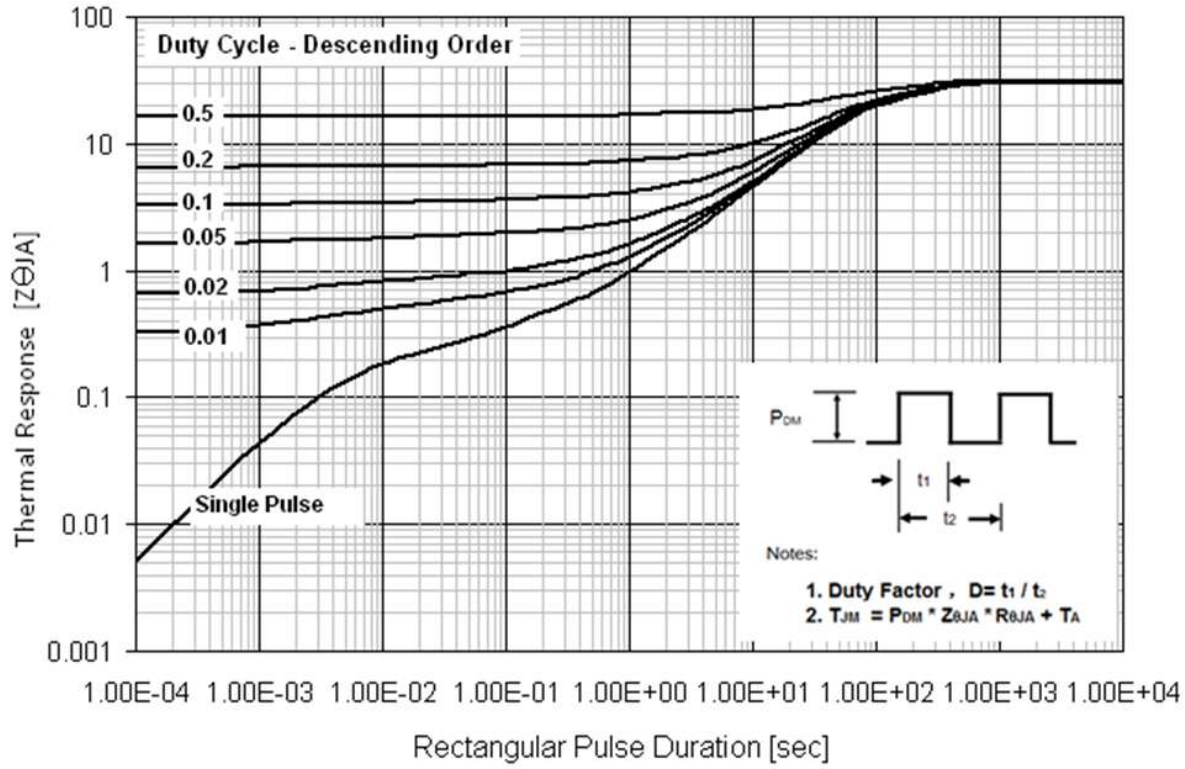
Maximum Drain Current vs. Case Temperature



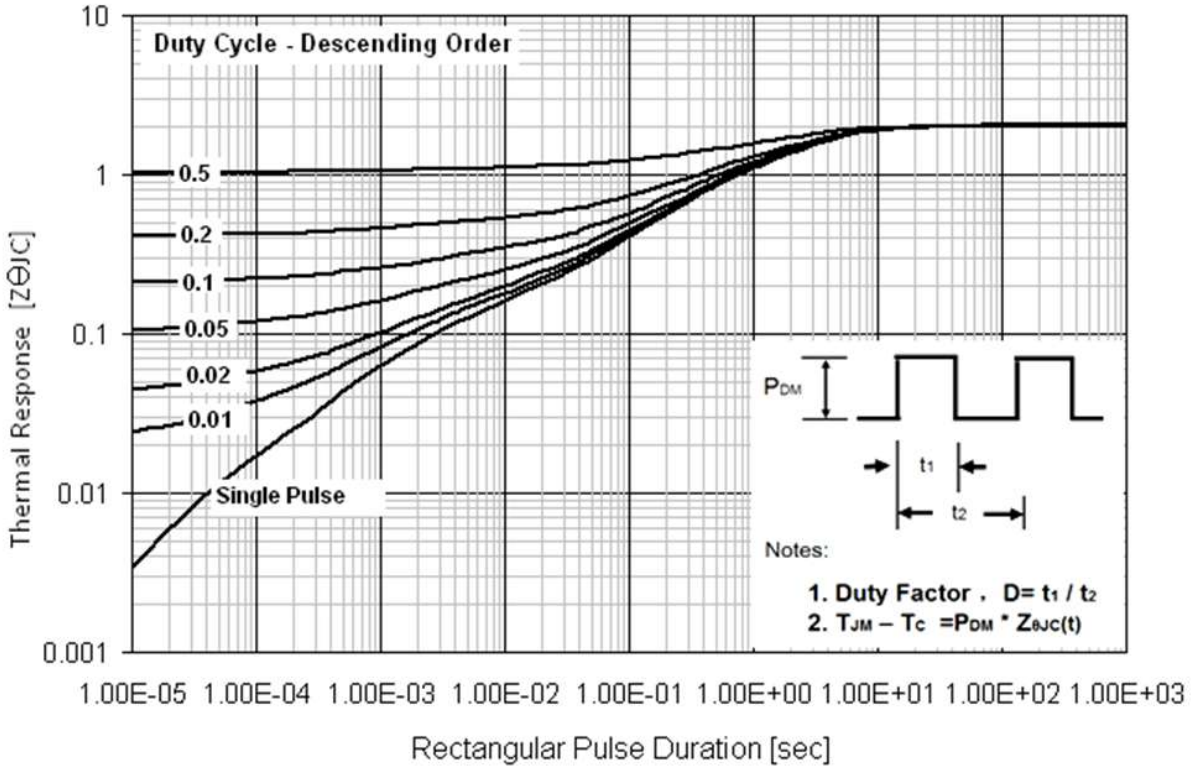
特征曲线 ELECTRICAL CHARACTERISTICS (curves)

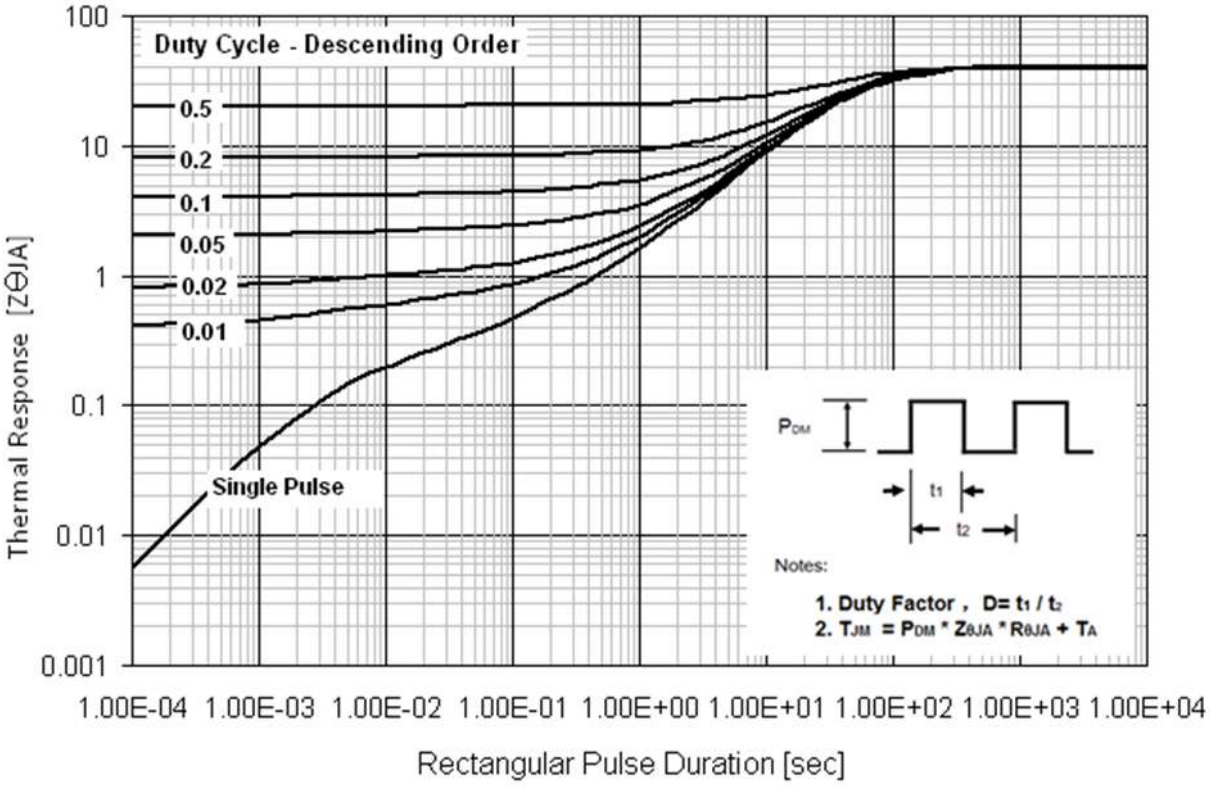
Transient Thermal Response Curve For JCS20N65WH





Transient Thermal Response Curve For JCS20N65FH

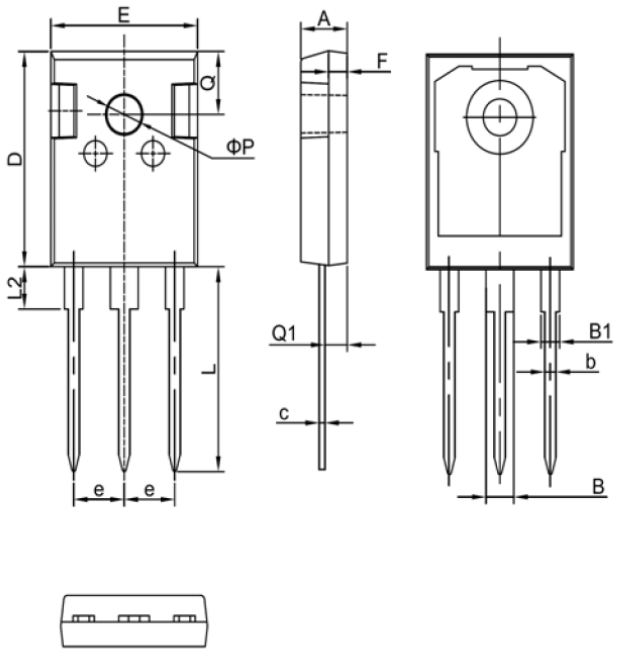




外形尺寸 PACKAGE MECHANICAL DATA

TO-247

单位 Unit：mm

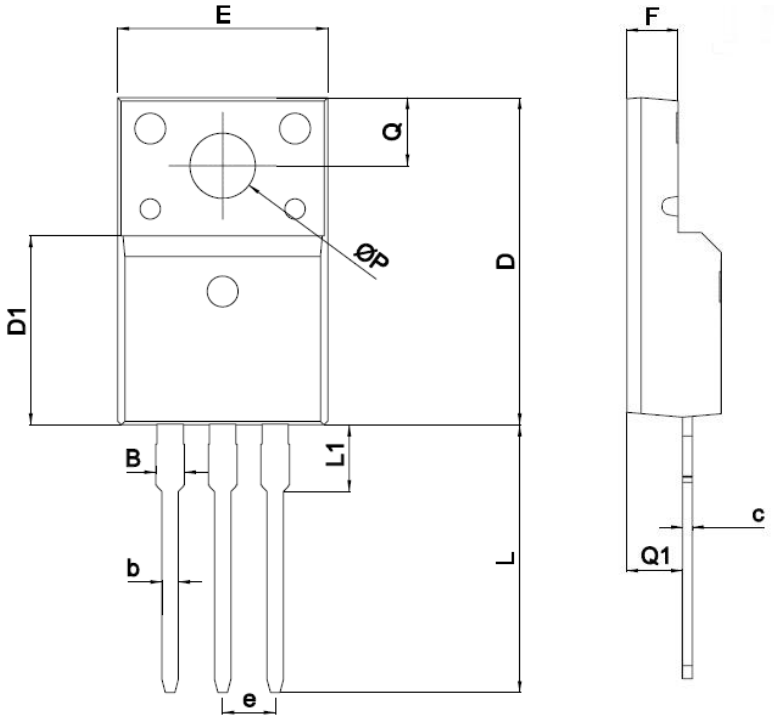


符号 symbol	MIN	MAX
A	4.90	5.10
B	2.95	3.35
B1	1.95	2.35
b	1.15	1.35
c	0.50	0.70
D	20.90	21.10
E	15.70	15.90
e	5.34	5.54
F	1.90	2.10
L	19.40	20.40
L2	4.03	4.23
Q	6.00	6.40
Q1	2.30	2.50
P	3.50	3.70

外形尺寸 **PACKAGE MECHANICAL DATA**

TO-220MF

单位 Unit：mm



SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B		1.47
b	0.7	0.9
c	0.45	0.60
D	15.67	16.07
D1	9.04	9.20
e	2.54TYPE	
E	9.96	10.36
F	2.34	2.74
L	12.58	13.38
L1	3.13	3.33
Q	3.2	3.4
Q1	2.56	2.96
ΦP	3.08	3.28